Elektronische Bauelemente

2SB647A

-1A , -120V

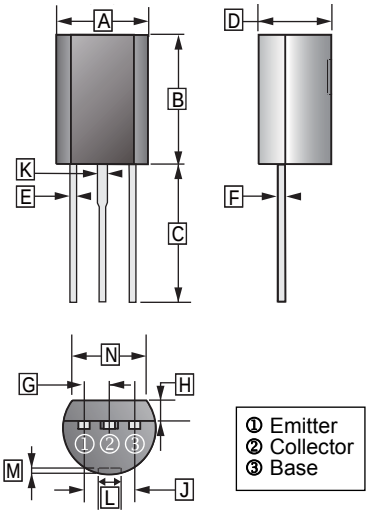
PNP Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

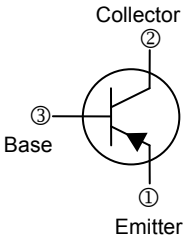
- Power Amplifier Applications .
- Low Frequency Power Amplifier

TO-92MOD



CLASSIFICATION OF h_{FE}

Product-Rank	2SB647A-B	2SB647A-C
Range	60~120	100~200



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.50	6.50	H	1.70	2.05
B	8.00	9.00	J	2.70	3.20
C	12.70	14.50	K	0.85	1.15
D	4.50	5.30	L	1.60 Max	
E	0.35	0.65	M	0.00	0.40
F	0.30	0.51	N	4.00 Min	
G	1.50 TYP.				

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-1	A
Collector Power Dissipation	P_C	0.9	W
Thermal Resistance, Junction To Ambient	$R_{\theta JA}$	139	°C/W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-120	-	-	V	I_C= -10μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100	-	-	V	I_C= -1mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E= -10μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	-10	μA	V_{CB}= -100V, I_E=0
DC Current Gain	h_{FE}	60	-	200		V_{CE}= -5V, I_C= -150mA
		30	-	-		V_{CE}= -5V, I_C= -500mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-1	V	I_C= -500mA, I_B= -50mA
Base to Emitter Saturation Voltage	V_{BE}	-	-	-1.5	V	V_{CE}= -5V, I_C= -150mA
Transition Frequency	f_T	-	140	-	MHz	V_{CE}= -5V, I_C= -150mA
Collector Output Capacitance	C_{ob}	-	20	-	pF	V_{CB}= -10V, I_E=0, f=1MHz

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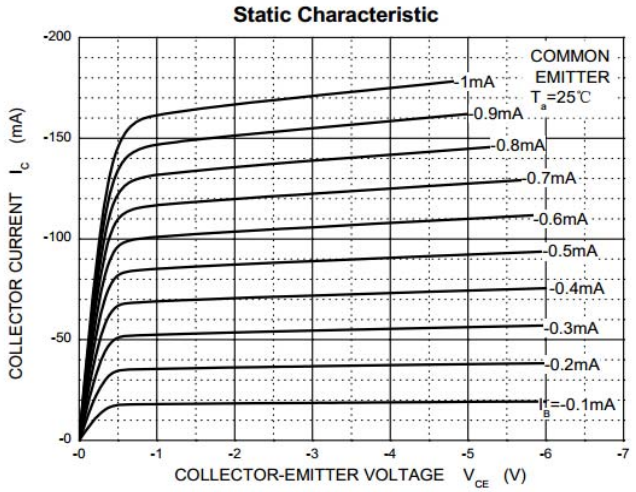
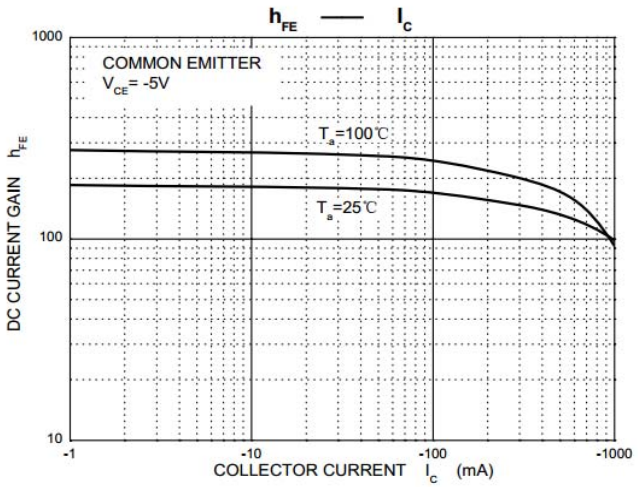
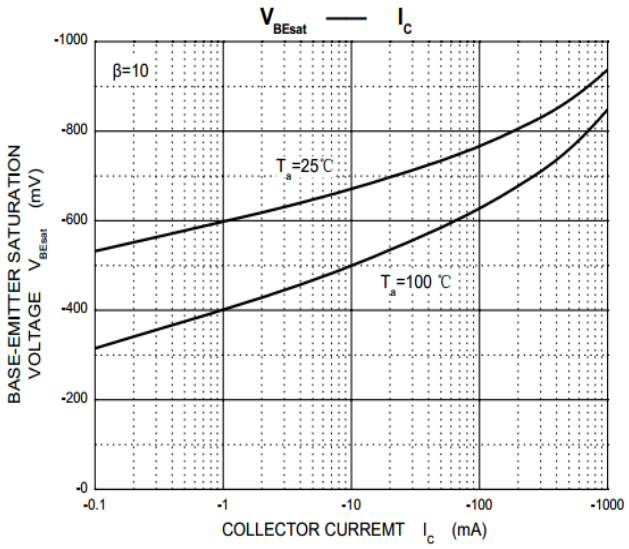
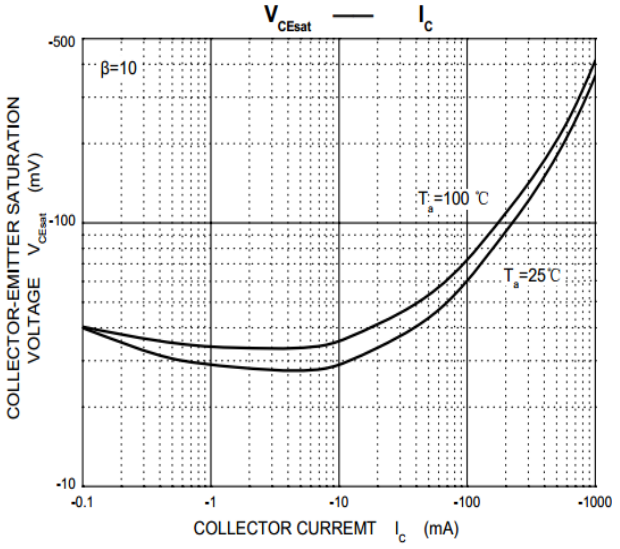
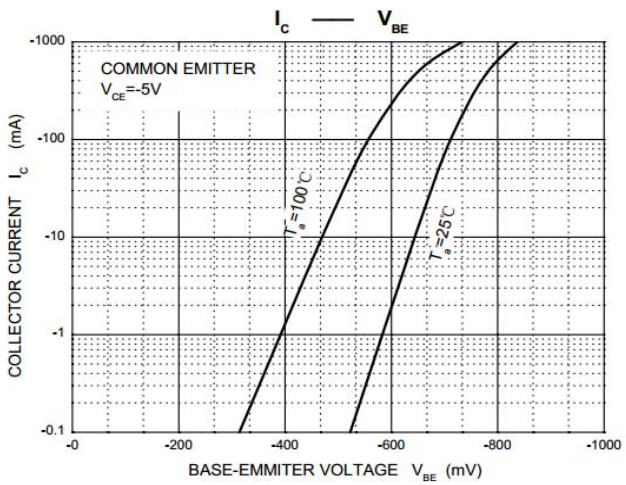
CHARACTERISTIC CURVES

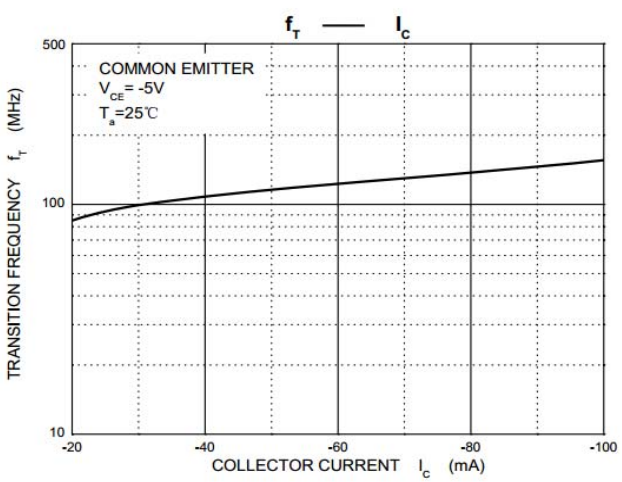












CHARACTERISTIC CURVES